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WITH AN ELECTRO OPTICAL INTEGRATED CIRCUIT

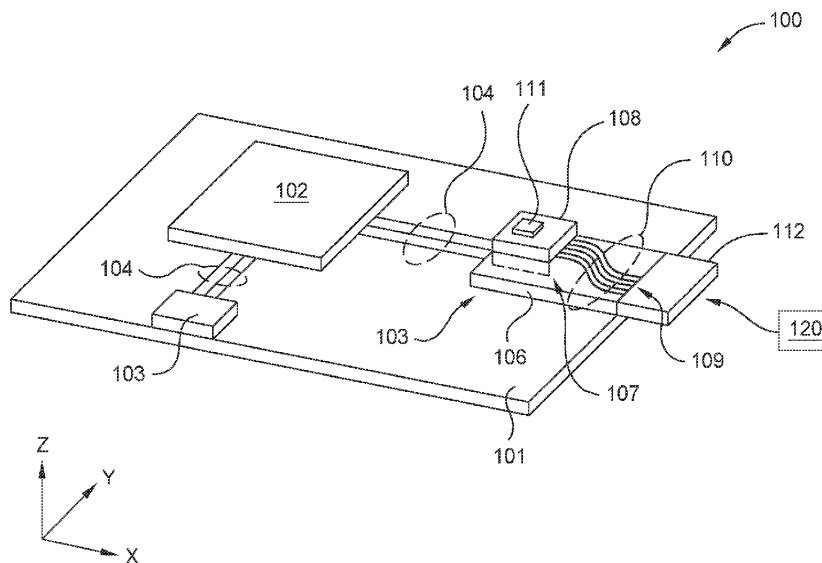


FIG. 1

(57) Abstract: Embodiments described herein relate to electronic and photonic integrated circuits and methods for fabricating integrated interconnect between electrical, opto-electrical and photonic devices. One or more optical silicon photonic devices described herein may be used in connection with one or more opto-electrical integrated circuits (opto-electrical chip) on a single package substrate to from a co- packaged optical and electrical device. The methods described herein enable high volume manufacturing of electrical, opto-elctrical and the optical silicon photonic devices having a plurality of optical structures, such as waveguides, formed on or integral with a photonic glass layer substrate.

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